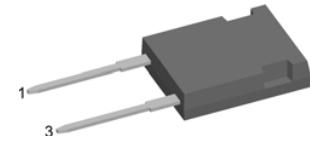
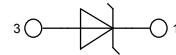


## Schottky Diode

High Performance Schottky Diode  
Low Loss and Soft Recovery  
Single Diode

**Part number**

DSS17-06CR



Backside: isolated

E72873

**Features / Advantages:**

- Very low V<sub>f</sub>
- Extremely low switching losses
- low I<sub>rm</sub> values
- Improved thermal behaviour
- High reliability circuit operation
- Low voltage peaks for reduced protection circuits
- Low noise switching

**Applications:**

- Rectifiers in switch mode power supplies (SMPS)
- Free wheeling diode in low voltage converters

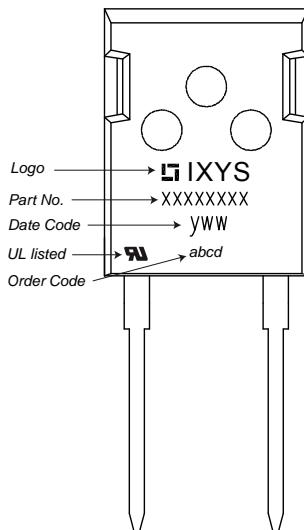
**Package:**

- Housing: ISOPLUS247
- Industry standard outline
- DCB isolated backside
- Isolation Voltage 3000 V
- Epoxy meets UL 94V-0
- RoHS compliant

Symbol	Definition	Conditions		Ratings		
				min.	typ.	max.
V <sub>RRM</sub>	max. repetitive reverse voltage		T <sub>VJ</sub> = 25°C			600 V
I <sub>R</sub>	reverse current	V <sub>R</sub> = 600 V	T <sub>VJ</sub> = 25°C		0.5 mA	
		V <sub>R</sub> = 600 V	T <sub>VJ</sub> = 125°C		5 mA	
V <sub>F</sub>	forward voltage	I <sub>F</sub> = 15 A	T <sub>VJ</sub> = 25°C		3.32 V	
		I <sub>F</sub> = 30 A			3.76 V	
		I <sub>F</sub> = 15 A	T <sub>VJ</sub> = 125°C		2.71 V	
		I <sub>F</sub> = 30 A			3.23 V	
I <sub>FAV</sub>	average forward current	rectangular d = 0.5	T <sub>C</sub> = 95°C		17 A	
V <sub>F0</sub> r <sub>F</sub>	threshold voltage slope resistance } for power loss calculation only		T <sub>VJ</sub> = 175°C		1.91 V	
					33.3 mΩ	
R <sub>thJC</sub>	thermal resistance junction to case				1.40 K/W	
T <sub>VJ</sub>	virtual junction temperature			-55	175 °C	
P <sub>tot</sub>	total power dissipation		T <sub>C</sub> = 25°C		105 W	
I <sub>FSM</sub>	max. forward surge current	t = 10 ms (50 Hz), sine	T <sub>VJ</sub> = 45°C		200 A	
C <sub>J</sub>	junction capacitance	V <sub>R</sub> = 400 V; f = 1 MHz	T <sub>VJ</sub> = 25°C		20 pF	

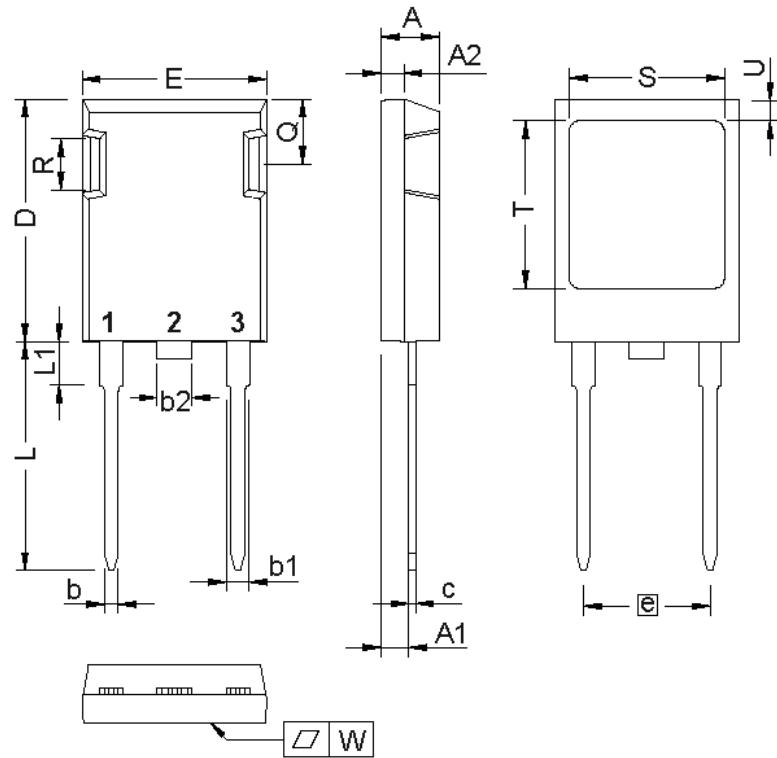
Symbol	Definition	Conditions	Ratings			
			min.	typ.	max.	
$I_{RMS}$	RMS current	per terminal			50	A
$R_{thCH}$	thermal resistance case to heatsink			0.25		K/W
$T_{stg}$	storage temperature		-55		150	°C
<b>Weight</b>				6		g
$F_c$	mounting force with clip		20		120	N
$V_{ISOL}$	isolation voltage	t = 1 second t = 1 minute	3600 3000			V
$d_{Spp/App}$	creepage   striking distance on surface   through air	terminal to terminal	5.5			mm
$d_{Spb/Abp}$	creepage   striking distance on surface   through air	terminal to backside	5.5			mm

### Product Marking



Ordering	Part Name	Marking on Product	Delivering Mode	Base Qty	Code Key
Standard	DSS17-06CR	DSS17-06CR	Tube	30	480266

## Outlines ISOPLUS247



Dim.	Millimeter		Inches	
	min	max	min	max
A	4.83	5.21	0.190	0.205
A1	2.29	2.54	0.090	0.100
A2	1.91	2.16	0.075	0.085
b	1.14	1.40	0.045	0.055
b1	1.91	2.15	0.075	0.085
b2	2.92	3.20	0.115	0.126
c	0.61	0.83	0.024	0.033
D	20.80	21.34	0.819	0.840
E	15.75	16.13	0.620	0.635
e	10.90	BSC	0.430	BSC
L	19.81	20.60	0.780	0.811
L1	3.81	4.38	0.150	0.172
L2	0.00	2.54	0.000	0.100
Q	5.59	6.20	0.220	0.244
R	4.32	4.85	0.170	0.191
S	13.21	13.72	0.520	0.540
T	15.75	16.26	0.620	0.640
U	1.65	2.03	0.065	0.080
W	-	0.10	-	0.004

Die konvexe Form des Substrates ist typ. < 0.04 mm über der Kunststoffoberfläche der Bauteilunterseite  
*The convex bow of substrate is typ. < 0.04 mm over plastic surface level of device bottom side*

Die Gehäuseabmessungen entsprechen dem Typ TO-247 AD gemäß JEDEC außer Schraubloch und  $L_{max}$ .  
*This drawing will meet all dimensions requirement of JEDEC outline TO-247 AD except screw hole and except  $L_{max}$ .*

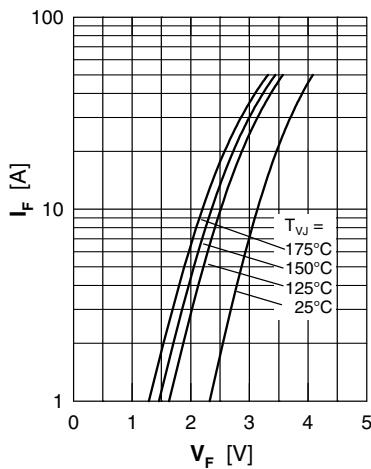


Fig. 1 Maximum forward voltage drop characteristics

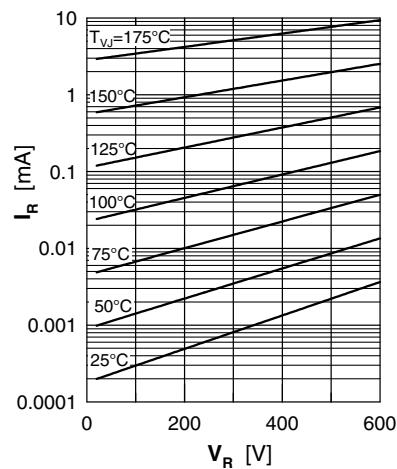


Fig. 2 Typ. reverse current  $I_R$  vs. reverse voltage  $V_R$

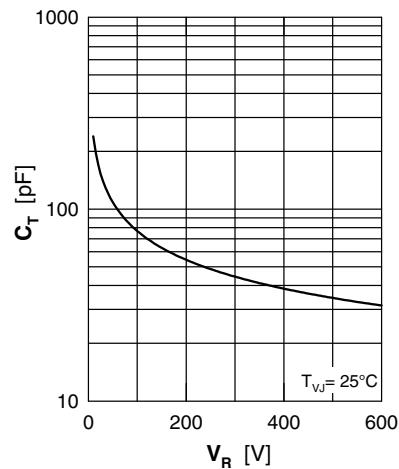


Fig. 3 Typ. junction capacitance  $C_T$  vs. reverse voltage  $V_R$

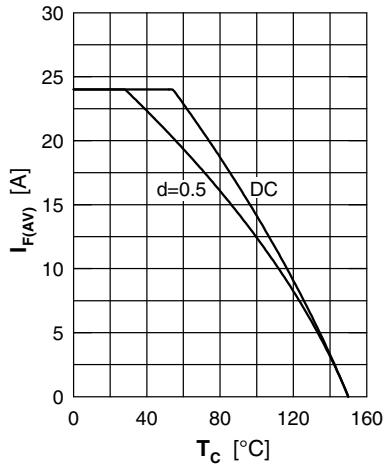


Fig. 4 Average forward current  $I_{F(AV)}$  vs. case temperature  $T_C$

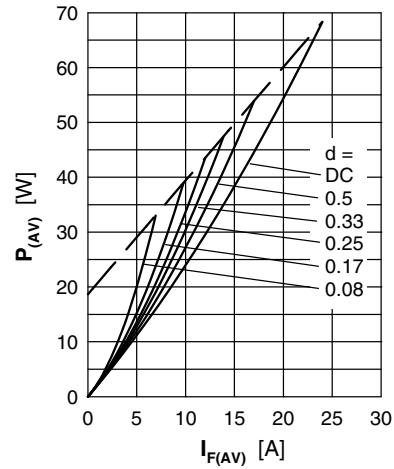
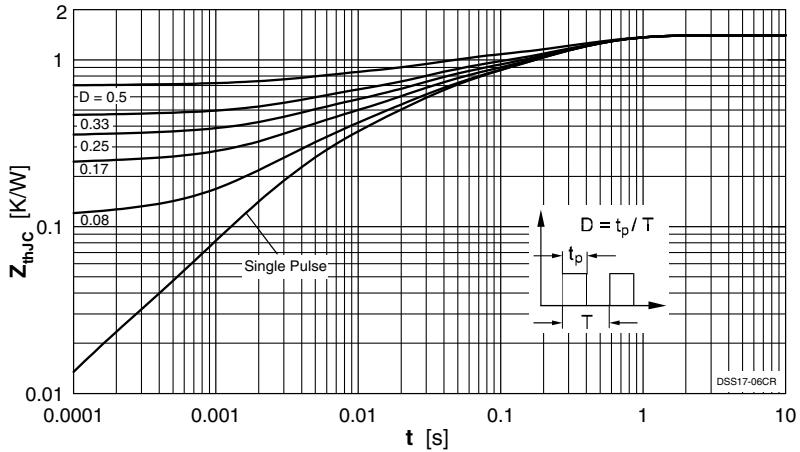


Fig. 5 Forward power loss characteristics



Note: All curves are per diode

Fig. 6 Transient thermal impedance junction to case at various duty cycles